

Notice of References Cited	Application/Control No. 10/572,680		Applicant(s)/Patent Under Reexamination TOMOZAWA ET AL.	
	Examiner Hoang-Quan Ho		Art Unit 2818	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-2002/0063256	05-2002	Lin, Ming-Der	257/79
*	B	US-2003/0164503	09-2003	Chen, Tzer-Perng	257/79
*	C	US-2002/0185732	12-2002	HO et al.	257/734
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)			
	U	Narayan et al. Formation of epitaxial Au/Ni/Au ohmic contacts to p-GaN. Nov. 18, 2002. Applied Physics Letters. Vol. 81, No. 21. Pgs. 3978-3980.			
	V	Liu et al. Effects of a Ni cap layer on transparent Ni/Au ohmic contacts to p-GaN. Jul/Aug 2002. J. Vac. Sci. Technol. B 20(4). Pgs. 1394-1401.			
	W				
	X				

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.